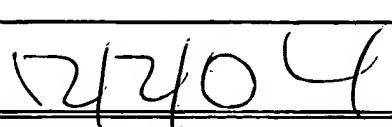


INFORMATION DISCLOSURE CITATION (Use several sheets if necessary) 		Docket Number (Optional) SALA:003		SERIAL NO.: 10/617,487			
		APPLICANT(s) SALAMA et al.					
		FILING DATE: July 11, 2003		Group Art Unit 2811			
U.S. PATENT DOCUMENTS							
EXAMINER INITIAL	REF	DOCUMENT NUMBER	DATE	NAME	CLASS	SUBCLASS	FILING DATE IF APPROPRIATE
ML	US	4,754,310	6/88	Coe	357	13	
ML	US	5,216,275	6/93	Chen	257	493	
ML	US	5,438,215	8/95	Tihanyi	257	401	
ML	US	2003/0190789	10/03	Salama et al.	438	286	
OTHER DOCUMENT(S) (Including Author, Title, Date, Pertinent Pages, Etc.)							
		ML	"High Voltage Thin Layer Devices (Resurf Devices)"; J.A. APPELS et al.; IEEE International Electron Device Meeting (IEDM); Dig. Tech Papers; pp. 238-241; 1979.				
		ML	"Theory of a novel voltage-sustaining layer for power devices"; X.B. CHEN et al.; Microelectronics Journal, Vol. 29; pp. 1005-1011; 1998.				
		ML	"COOLMOS™ - a new milestone in high voltage Power MOS"; L. LORENZ et al.; Proceedings of the 11 th International Symposium on Power Semiconductor Devices and ICs (ISPSD); pp. 3-10; 1999.				
		ML	"Super Junction LDMOST in Silicon-On-Sapphire Technology (SJ-LDMOST)"; Sameh NASSIF-KHALIL et al.; International Symposium on Power Semiconductor Devices and ICs (ISPSD), Proceedings; pp. 81-84; 2002.				
		ML	"170V Super Junction - LDMOST in a 0.5 μ m Commercial CMOS/SOS Technology"; S.G. NASSIF-KHALIL et al.; International Symposium on Power Semiconductor Devices and ICs (ISPSD), Proceedings, accepted for publication; 4 pages.				
		ML	"Extended (180V) Voltage in 0.6 μ m Thin-Layer-SOI A-BCD3 Technology on 1 μ m BOX for Display, Automotive & Consumer Applications"; A.W. LUDIKHUIZE et al.; International Symposium on Power Semiconductor Devices and ICs (ISPSD), Proceedings; pp. 77-80; 2002.				
		ML	"A Versatile 700-1200-V IC Process for Analog and Switching Applications"; Adriaan LUDIKHUIZE; IEEE Transactions on Electron Devices, vol. 38; pp. 1582-1589; 1991.				
		ML	"Experimental Results and Simulation Analysis of 250V Super Trench Power MOSFET (STM)"; T. NITTA et al.; International Symposium on Power Semiconductor Devices and ICs (ISPSD), Proceedings; pp. 77-80; 2000.				
		ML	"Super-Junction LDMOST on a Silicon-on-Sapphire Substrate"; S. NASSIF-KHALIL et al.; IEEE Transactions on Electron Devices, Vol. 50, No. 5; May 2003; pp. 1385-1391.				
EXAMINER			DATE CONSIDERED				

*EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.